



40V P-Channel Enhancement Mode MOSFET

Voltage

-40 V

Current

-45 A

Features

- R_{DS(ON)}, V_{GS}@-10V, I_D@-15A<17mΩ
- $R_{DS(ON)}$, $V_{GS}@-4.5V$, $I_D@-10A<25m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case: DFN5060-8L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0028 ounces, 0.08 grams

DFN5060-8L

$\textbf{Maximum Ratings and Thermal Characteristics} \; (\textbf{T}_{\textbf{A}} = 25 ^{\circ} \textbf{C} \; \text{unless otherwise noted})$

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	-40	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current (Note 4)	T _C =25°C	I _D	-45	А	
	T _C =100°C		-28		
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	-135		
Power Dissipation	T _C =25°C	Po	63	10/	
	T _C =100°C		25	W	
Continuous Drain Current (Note 4)	T _A =25°C	I _D	-8.5		
	T _A =70°C		-7	Α	
Power Dissipation	T _A =25°C	Po	2	10/	
	T _A =70°C		1.3	W	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	2	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

• Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-40	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=-250uA$	-1	-1.6	-2.5		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-15A	_	14	17	mΩ	
		V _{GS} =-4.5V, I _D =-10A	-	20	25		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-40V, V _{GS} =0V	-	-	-1	uA	
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA	
Dynamic (Note 6)							
Total Gate Charge	Q_g	V _{DS} =-32V, I _D =-10A, V _{GS} =-4.5V ^(Note 1,2)	-	19	-	nC	
Gate-Source Charge	Q_{gs}		-	5.3	-		
Gate-Drain Charge	Q_gd		-	6.6	-		
Input Capacitance	Ciss	V _{DS} =-25V, V _{GS} =0V,	-	2030	-	pF	
Output Capacitance	Coss		-	190	-		
Reverse Transfer Capacitance	Crss	I=IIVITZ	-	139	-		
Turn-On Delay Time	td _(on)	V_{DS} =-20V, I_{D} =-1A, V_{GS} =-10V, R_{G} =6 Ω (Note 1,2)	-	8.6	-		
Turn-On Rise Time	t _r		-	9.6	-	ns	
Turn-Off Delay Time	td _(off)		-	77	-		
Turn-Off Fall Time	t _f		-	39	-		
Drain-Source Diode							
Maximum Continuous Drain-Source	,			-	-45	А	
Diode Forward Current	I _S		-				
Diode Forward Voltage	V_{SD}	I _S =-1A,V _{GS} =0V	-	-0.7	-1	V	

NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J=25°C.
- 4. The maximum current rating is package limited.
- 5. Roja is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

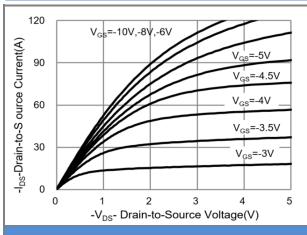


Fig.1 On-Region Characteristics

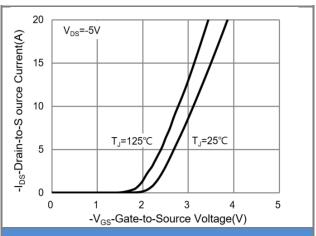


Fig.2 Transfer Characteristics

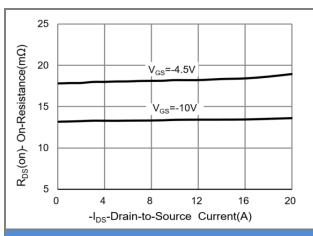


Fig.3 On-Resistance vs. Drain Current

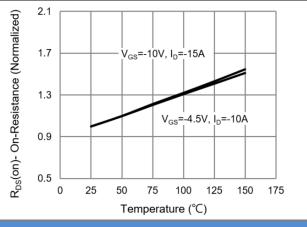


Fig.4 On-Resistance vs. Junction temperature

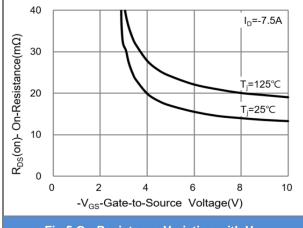


Fig.5 On-Resistance Variation with V_{GS}

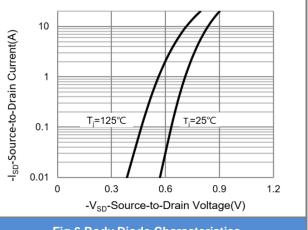


Fig.6 Body Diode Characteristics





TYPICAL CHARACTERISTIC CURVES

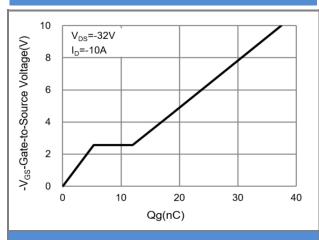


Fig.7 Gate-Charge Characteristics

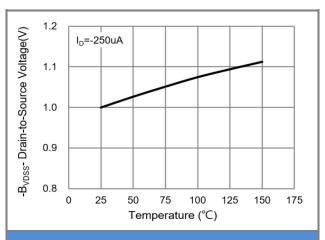


Fig.8 Breakdown Voltage Variation vs. Temperature

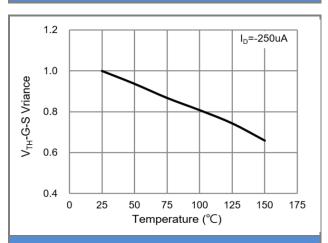


Fig.9 Threshold Voltage Variation with Temperature

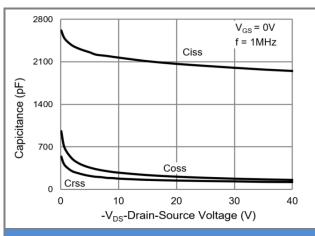


Fig.10 Capacitance vs. Drain-Source Voltage

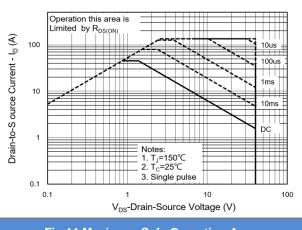


Fig.11 Maximum Safe Operating Area

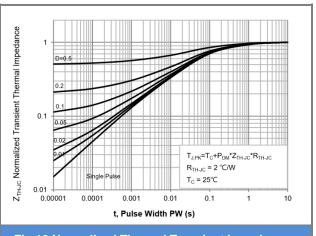


Fig.12 Normalized Thermal Transient Impedance

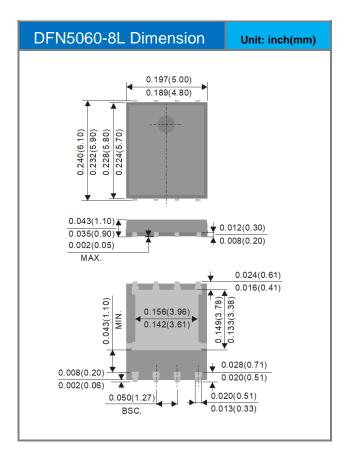


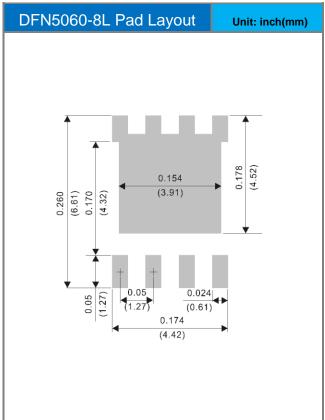


Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJQ5445-AU_R2_000A1	DFN5060-8L	3000pcs / 13" reel	Q5445	Halogen free

Packaging Information & Mounting Pad Layout









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